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SPT36-C

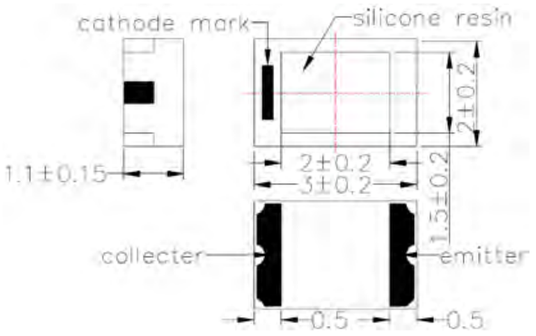
TECHNICAL DATA

Silicone Photo-Transistor, SMD package

SPT36-C is a surface mount type photo-transistor containing a chip with 0.6x0.6 mm active area, mounted into a ceramic package and covered with silicone. This device is featuring excellent responsibility of 20 μs and a high photocurrent. It's designed to be easy of setting up optically with a wide angle of half sensitivity of ±40 degrees.

Specifications

• Spectral Responsivity (Peak):	900 nm
• Chip Size:	0.8 x 0.8 mm
• Active Area:	0.6 x 0.6 mm
• Package:	SMD
Type:	Ceramics
Resin Material:	Silicone



(Unit: mm)

Absolute Maximum Ratings (T_A=25°C)

Item	Symbol	Value	Unit
C-E Breakdown Voltage	V_{CEO}	30	V
E-C Breakdown Voltage	V_{ECO}	5	V
Collector Current	I_C	10	mA
Collector Dissipation	P_C	50	mW
Operating Temperature	T_{opr}	-25 … +125	°C
Storage Temperature	T_{stg}	-30 … +100	°C
Soldering Temperature *[1]	T_{sol}	240	°C

*[1] must be completed within 3 seconds

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Photo Current	I_L	V_{CE}=5V, L=1000Lx	1	3	-	mA
Collector Dark Current	I_D	V_{CE}=5V	-	-	200	nA
Collector-Emitter Satu. Voltage	$V_{CE(S)}$	I_C=2mA, L=1000Lx	-	-	0.3	V
Spectral Responsivity (Peak)	λ_P		-	900	-	nm
Half Angle of Sensitivity	$\Theta_{1/2}$			±40	-	deg
Rise Time (10-90%)	t_r	R_L=1KΩ, V_R=5V I_C=1mA	-	20	-	μs
Fall Time (10-90%)	t_f		-	20	-	μs

Note: The above specifications are for reference purpose only and subjected to change without prior notice.